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(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38190 Bernin (FR).

(72) Inventors; and

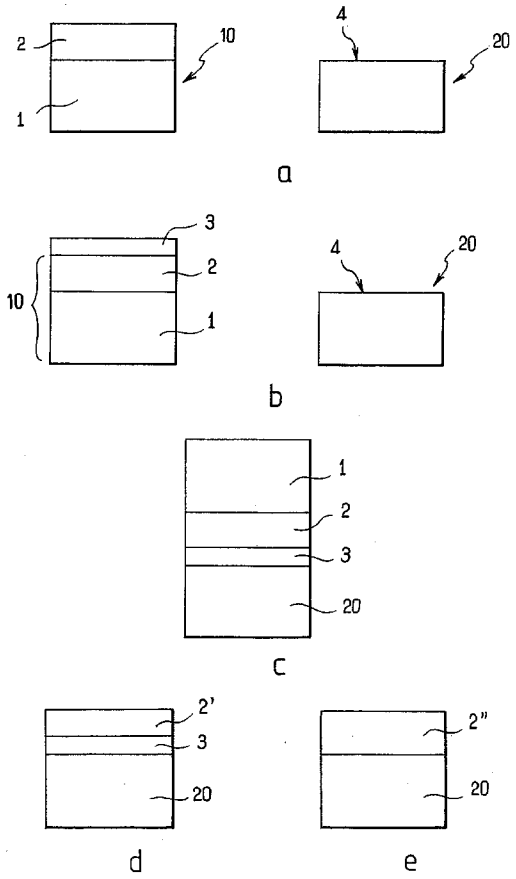
(75) Inventors/Applicants *(for US only)*: **DAVAL, Nicolas** [FR/FR]; 15, boulevard du Maréchal Leclerc, F-38000 Grenoble (FR). **GHYSELEN, Bruno** [FR/FR]; 58, rue Georges Maeder, F-38170 Seyssinet (FR). **AULNETTE, Cécile** [FR/FR]; 3, Place des Tilleuls, F-38000 Grenoble (FR). **RAYSSAC, Olivier** [FR/FR]; 7, chemin Chapitre, F-38100 Grenoble (FR). **CAYREFOURCQ, Ian** [FR/FR]; 74 Chemin du Theys, F-38330 Saint Nazaire Les Eymes (FR).

(74) Agents: **MARTIN, Jean-Jacques** et al.; Cabinet Regimbeau, 20, rue de Chazelles, F-75847 Paris Cedex 17 (FR).

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(54) Title: INDIRECT BONDING WITH DISAPPEARANCE OF THE BONDING LAYER



(57) Abstract: The invention provides a method of producing a structure comprising a thin layer (2") of semiconductive material on a support substrate (20), said thin layer (2") being obtained from a donor substrate (10) comprising an upper layer (2) of semiconductor material, the method being characterized in that it comprises: - forming on said upper layer (2) a bonding layer (3) of a material that accepts diffusion of an element of the material of the upper layer (2); - cleaning said bonding layer (3) for mastering its bonding adhesion; - bonding the donor substrate (10), from the side of the bonding layer (3) previously formed on the upper layer (2) and cleaned, to the support substrate (20); and - diffusing said element from the upper layer into the bonding layer to homogenize the concentration of said element in the bonding layer and said upper layer, to constitute said thin layer (2") of the structure with said bonding layer and said upper layer.

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